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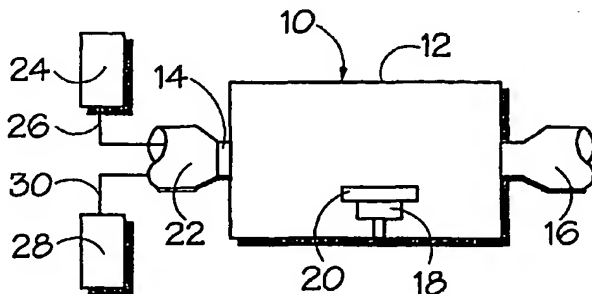
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(54) Title: METHOD AND APPARATUS FOR FORMING EPITAXIAL LAYERS



(57) Abstract: The present invention provides a method of depositing epitaxial layers based on Group IV elements on a silicon substrate by Chemical Vapor Deposition, wherein nitrogen or one of the noble gases is used as a carrier gas, and the invention further provides a Chemical Vapor Deposition apparatus (10) comprising a chamber (12) having a gas input port (14) and a gas output port (16), and means (18) for mounting a silicon substrate within the chamber (12), said apparatus further including a gas source connected to the input port and arranged to provide nitrogen or a noble gas as a carrier gas.

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C. DOCUMENTS CONSIDERED TO BE RELEVANT

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| C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT | | |
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